

## KSC2073

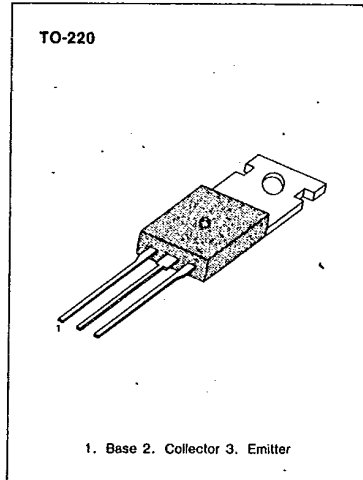
## NPN EPITAXIAL SILICON TRANSISTOR

## TV VERTICAL DEFLECTION OUTPUT

- Complement to KSA940
- Collector-Base Voltage  $V_{CBO} = 150V$

ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	150	V
Collector-Emitter Voltage	$V_{CEO}$	150	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1.5	A
Collector Dissipation ( $T_c = 25^\circ C$ )	$P_C$	25	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 ~ 150	$^\circ C$



3

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = 500\mu A, I_E = 0$	150			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 10mA, I_B = 0$	150			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = 500\mu A, I_C = 0$	5			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 120V, I_E = 0$			10	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 0.5A$	40	75	140	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1	V
Current Gain Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 0.5A$		4		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$		50		pF

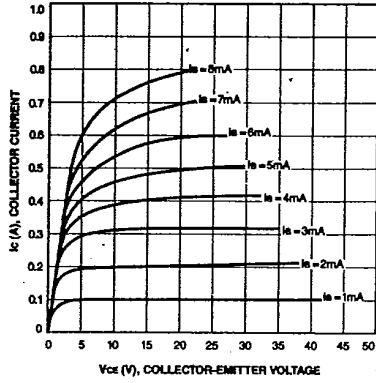


KSC2073

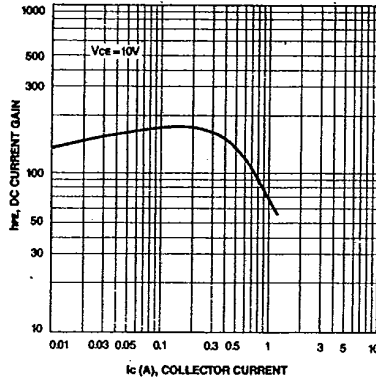
NPN EPITAXIAL SILICON TRANSISTOR

T-33-09

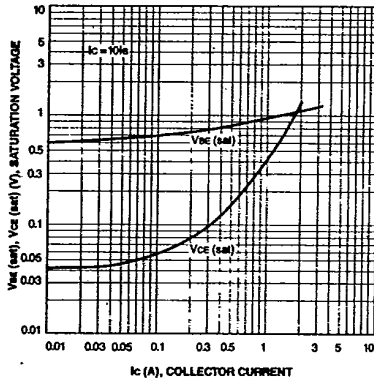
STATIC CHARACTERISTIC



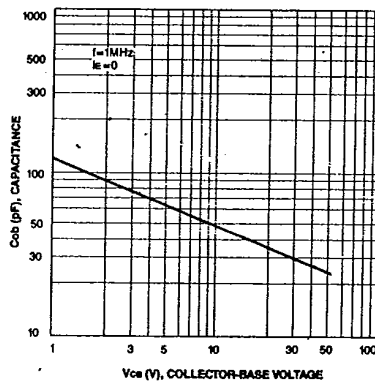
DC CURRENT GAIN



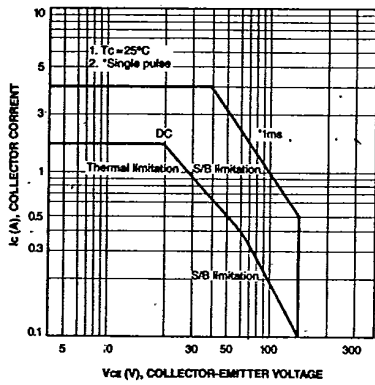
BASE-EMITTER SATURATION VOLTAGE  
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



SAFE OPERATING AREA



POWER DERATING

